EB13E2 Series



REGULATORY COMPLIANCE

Lead Free	EU RoHS	China RoHS	REACH
\bigotimes	2011/65 + 2015/863	e	ѕѵнс
COMPLIANT	COMPLIANT	COMPLIANT	COMPLIANT



ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) LVCMOS (CMOS) 3.3Vdc 4 Pad 2.5mm x 3.2mm Ceramic Surface Mount (SMD)

ELECTRICAL SPECIFICATIONS			
Nominal Frequency	1.024MHz to 66.6666MHz		
Frequency Tolerance/Stability	Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration ±100ppm Maximum over -20°C to +70°C ±50ppm Maximum over -20°C to +70°C ±25ppm Maximum over -20°C to +70°C ±20ppm Maximum over -20°C to +70°C ±100ppm Maximum over -20°C to +85°C ±50ppm Maximum over -40°C to +85°C ±25ppm Maximum over -40°C to +85°C ±20ppm Maximum over -40°C to +85°C		
Supply Voltage	3.3Vdc ±5%		
Input Current	3mA Maximum over Nominal Frequency of 1.024MHz to 9.999999MHz 4mA Maximum over Nominal Frequency of 10MHz to 19.9999999MHz 5mA Maximum over Nominal Frequency of 20MHz to 39.999999MHz 6mA Maximum over Nominal Frequency of 40MHz to 50MHz 9mA Maximum over Nominal Frequency of 50.000001MHz to 66.6666MHz		
Output Voltage Logic High (V _{Oh})	IOH = -4mA 90% of Vdd Minimum		
Output Voltage Logic Low (V _{ol})	IOL = +4mA 10% of Vdd Maximum		
Rise/Fall Time	Measured at 20% to 80% of waveform 5nSec Maximum over Nominal Frequency of 1.024MHz to 24MHz 4nSec Maximum over Nominal Frequency of 24.000001MHz to 50MHz 3nSec Maximum over Nominal Frequency of 50.000001MHz to 66.6666MHz		
Duty Cycle	Measured at 50% of Waveform 50 ±5(%)		
Load Drive Capability	15pF Maximum		
Output Logic Type	CMOS		
Logic Control / Additional Output	Tri-State (High Impedance)		
Tri-State Input Voltage (Vih and Vil)	80% of Vdd Minimum or No Connect to Enable Output, 20% of Vdd Maximum to Disable Output (High Impedance)		
Standby Current	Disabled Output: High Impedance 10μΑ Maximum		
RMS Phase Jitter	Fj = 12kHz to 20MHz 1pSec Maximum		
Start Up Time	10mSec Maximum		
Storage Temperature Range	-55°C to +125°C		



PART NUMBERING GUIDE

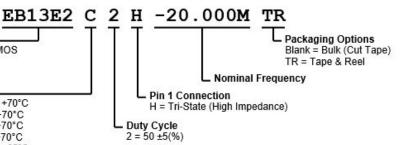


Quartz Crystal Clock Oscillators XO (SPXO) LVCMOS (CMOS) 3.3Vdc 4 Pad 2.5mm x 3.2mm Ceramic Surface Mount (SMD)

> Frequency Tolerance/Stability _ C = ±100ppm Maximum over -20°C to +70°C

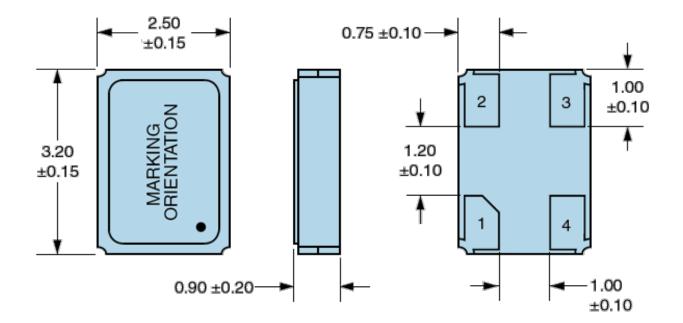
- $\begin{array}{l} D = \pm 50 \text{ppm Maximum over } -20^{\circ}\text{C to } +70^{\circ}\text{C} \\ \text{E} = \pm 25 \text{ppm Maximum over } -20^{\circ}\text{C to } +70^{\circ}\text{C} \\ \text{F} = \pm 20 \text{ppm Maximum over } -20^{\circ}\text{C to } +70^{\circ}\text{C} \end{array}$

- G = ±100ppm Maximum over -40°C to +85°C
- $H = \pm 20$ ppm Maximum over -40°C to +85°C J = ± 25 ppm Maximum over -40°C to +85°C K = ± 20 ppm Maximum over -40°C to +85°C

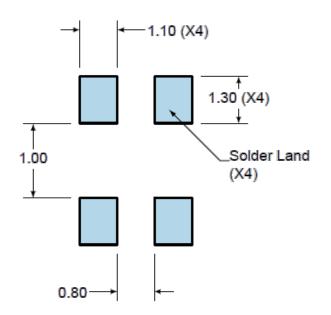




MECHANICAL DIMENSIONS



SUGGESTED SOLDER PAD LAYOUT



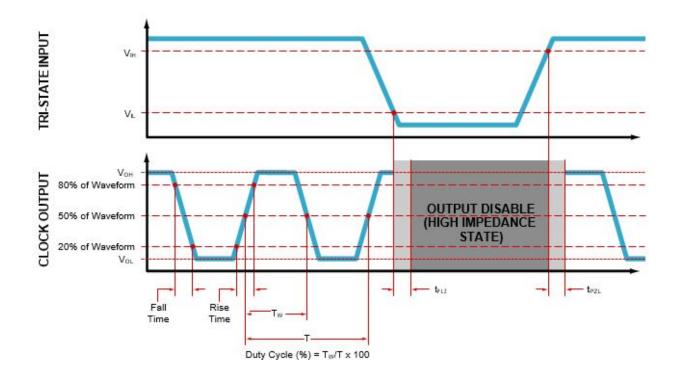
PIN	CONNECTION
1	Tri-State
2	Case/Ground
3	Output
4	Supply Voltage

All Tolerances are ±0.1

All Dimensions in Millimeters

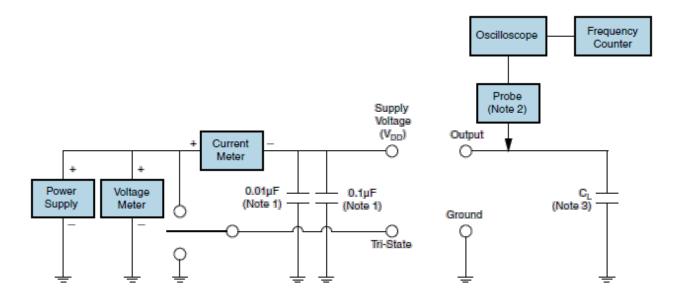


OUTPUT WAVEFORM & TIMING DIAGRAM





TEST CIRCUIT FOR CMOS OUTPUT



- **Note 1:** An external 0.1μF low frequency tantalum bypass capacitor in parallel with a 0.01μF high frequency ceramic bypass Capacitor close to the package ground and V_{DD} pin is required.
- **Note 2:** A low input capacitance (<12pF), 10X Attentuation Factor, High Impedance (>10Mohms), and High bandwidth (>300MHz) Passive probe is recommended.
- Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance. See applicable specification sheet for 'Load Drive Capability'.

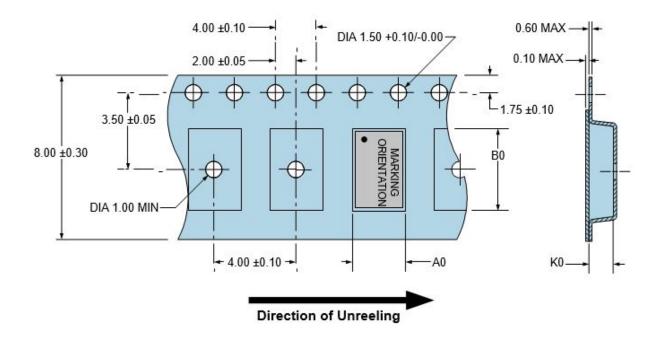
EB13E2 Series

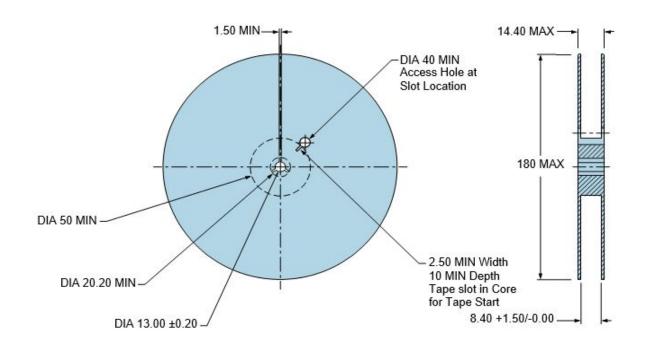


TAPE & REEL DIMENSIONS

Quantity per Reel: 1000 Units All Dimensions in Millimeters

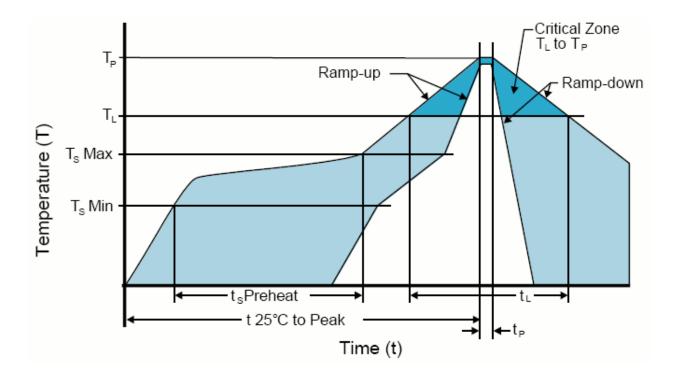
Compliant to EIA-481







RECOMMENDED SOLDER REFLOW METHOD



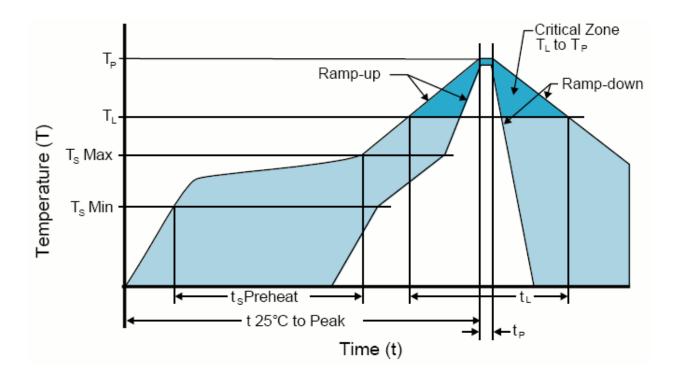
HIGH TEMPERATURE INFRARED/CONVECTION		
T_s MAX to T_L (Ramp-up Rate)	3°C/Second Maximum	
Preheat		
- Temperature Minimum (Ts MIN)	150°C	
- Temperature Typical (T _s TYP)	175°C	
 Temperature Maximum(T_s MAX) 	200°C	
- Time (t _s)	60 - 180 Seconds	
Ramp-up Rate (T _L to T _P)	3°C/Second Maximum	
Time Maintained Above:		
- Temperature (T∟)	217°C	
- Time (t _L)	60 - 150 Seconds	
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum	
Target Peak Temperature(T _P Target)	250°C +0/-5°C	
Time within 5°C of actual peak (t _p)	20 - 40 Seconds	
Ramp-down Rate	6°C/Second Maximum	
Time 25°C to Peak Temperature (t)	8 Minutes Maximum	
Moisture Sensitivity Level	Level 1	
Additional Notes	Temperatures shown are applied to body of device.	

High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)



RECOMMENDED SOLDER REFLOW METHOD



LOW TEMPERATURE INFRARED/CONVECTION		
T_s MAX to T_L (Ramp-up Rate)	5°C/Second Maximum	
Preheat		
- Temperature Minimum (Ts MIN)	N/A	
- Temperature Typical (T _s TYP)	150°C	
 Temperature Maximum(T_s MAX) 	N/A	
- Time (t _s)	60 - 120 Seconds	
Ramp-up Rate (T _L to T _P)	5°C/Second Maximum	
Time Maintained Above:		
- Temperature (T∟)	150°C	
- Time (t∟)	200 Seconds Maximum	
Peak Temperature (T _P)	240°C Maximum	
Target Peak Temperature (T _P Target)	240°C Maximum 2 Times / 230°C Maximum 1 Time	
Time within 5°C of actual peak (t _p)	10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time	
Ramp-down Rate	5°C/Second Maximum	
Time 25°C to Peak Temperature (t)	N/A	
Moisture Sensitivity Level	Level 1	
Additional Notes	Temperatures shown are applied to body of device.	

Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)